

## PNP General Purpose Transistor

BC857B

## ● Features

- 1)  $BV_{CEO} < -45V$  ( $I_C = -1mA$ )
- 2) Complements the BC847B.

### ● Package, marking, and packaging specifications

Part No.	BC857B
Packging type	SST3
Marking	G3F
Code	T116
Basic ordering unit (pieces)	3000

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	$V_{CB0}$	—50	V	
Collector-emitter voltage	$V_{CE0}$	—45	V	
Emitter-base voltage	$V_{EB0}$	—5	V	
Collector current	$I_c$	—0.1	A	
Collector power dissipation	$P_c$	0.2	W	*
		0.35		
Junction temperature	$T_J$	150	°C	
Storage temperature	$T_{stg}$	—55~+150	°C	

\* When mounted on a 7 x 5 x 0.6mm ceramic board.

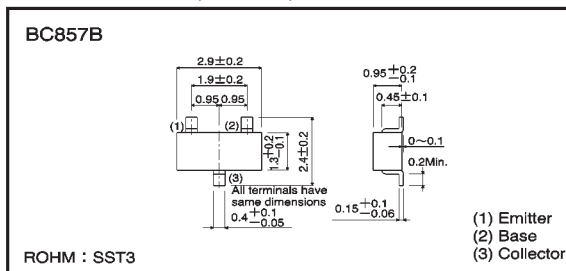
### ● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-50	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	-45	—	—	V	$I_C = -1mA$
Emitter-base breakdown voltage	$BV_{EBO}$	-5	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	$I_{CBO}$	—	—	-15	nA	$V_{CB} = -30V$
		—	—	-4		$V_{CB} = -30V, T_A = 150^\circ C$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.3	V	$I_C/I_E = -10mA/-0.5mA$
		—	—	-0.65		$I_C/I_E = -100mA/-5mA$
Base-emitter saturation voltage	$V_{BE(on)}$	-0.6	—	-0.75	V	$V_{CE}/I_C = -5V/-10mA$
DC current transfer ratio	$h_{FE}$	210	—	480	—	$V_{CE}/I_C = -5V/-2mA$
Transition frequency	$f_T$	—	250	—	MHz	$V_{CE} = -5V, I_E = 20mA, f = 100MHz$
Collector output capacitance	$C_{ob}$	—	4.5	—	pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

### ● Electrical characteristic curves

The electrical characteristic curves for these products are the same as those of BC858BW and BC858B. Refer to pages 603 to 606.

●External dimensions (Units : mm)



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